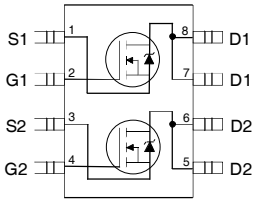
International
IOR Rectifier

IRF7313PbF-1

HEXFET® Power MOSFET

V_{DS}	30	V
$R_{DS(on)\ max}$ (@V_{GS} = 10V)	0.029	Ω
$Q_{g\ (typical)}$	22	nC
I_D (@T_A = 25°C)	6.5	A



Top View


SO-8

Features	⇒	Benefits
Industry-standard pinout SO-8 Package		Multi-Vendor Compatibility
Compatible with Existing Surface Mount Techniques		Easier Manufacturing
RoHS Compliant, Halogen-Free		Environmentally Friendlier
MSL1, Industrial qualification		Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7313PbF-1	SO-8	Tube/Bulk	95	IRF7313PbF-1
		Tape and Reel	4000	IRF7313TRPbF-1

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current⑤	T_A = 25°C	I_D	6.5	A
	T_A = 70°C		5.2	
Pulsed Drain Current		I_{DM}	30	
Continuous Source Current (Diode Conduction)		I_S	2.5	
Maximum Power Dissipation ⑤	T_A = 25°C	P_D	2.0	W
	T_A = 70°C		1.3	
Single Pulse Avalanche Energy ②		E_{AS}	82	mJ
Avalanche Current		I_{AR}	4.0	A
Repetitive Avalanche Energy		E_{AR}	0.20	mJ
Peak Diode Recovery dv/dt ③		dv/dt	5.8	V/ ns
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to + 150	℃

Thermal Resistance Ratings

Parameter	Symbol	Limit	Units
Maximum Junction-to-Ambient⑤	$R_{\theta JA}$	62.5	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.022	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	0.023	0.029	Ω	V_{GS} = 10V, I_D = 5.8A ④
		–––	0.032	0.046		V_{GS} = 4.5V, I_D = 4.7A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	–––	–––	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	–––	14	–––	S	V_{DS} = 15V, I_D = 5.8A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	1.0	µA	V_{DS} = 24V, V_{GS} = 0V
		–––	–––	25		V_{DS} = 24V, V_{GS} = 0V, T_J = 55°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -20V
Q_g	Total Gate Charge	–––	22	33	nC	I_D = 5.8A
Q_{gs}	Gate-to-Source Charge	–––	2.6	3.9		V_{DS} = 15V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	6.4	9.6		V_{GS} = 10V, See Fig. 10 ④
$t_{d(on)}$	Turn-On Delay Time	–––	8.1	12	ns	V_{DD} = 15V
t_r	Rise Time	–––	8.9	13		I_D = 1.0A
$t_{d(off)}$	Turn-Off Delay Time	–––	26	39		R_G = 6.0Ω
t_f	Fall Time	–––	17	26		R_D = 15Ω ④
C_{iss}	Input Capacitance	–––	650	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	320	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	130	–––		f = 1.0MHz, See Fig. 9

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	30		
V_{SD}	Diode Forward Voltage	–––	0.78	1.0	V	T_J = 25°C, I_S = 1.7A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	–––	45	68	ns	T_J = 25°C, I_F = 1.7A
Q_{rr}	Reverse RecoveryCharge	–––	58	87	nC	di/dt = 100A/µs ③

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 10mH, R_G = 25Ω, I_{AS} = 4.0A.

③ $I_{SD} \leq$ 4.0A, di/dt ≤ 74A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 150°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ Surface mounted on FR-4 board, t ≤ 10sec.

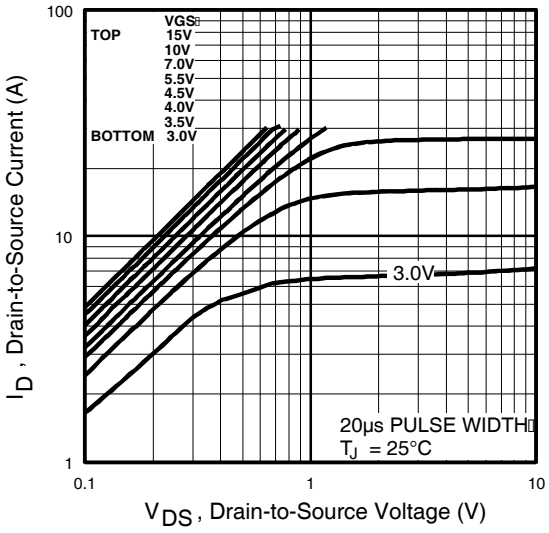


Fig 1. Typical Output Characteristics

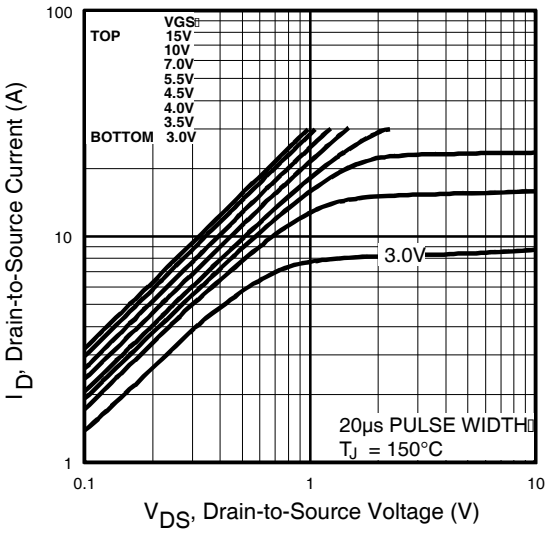


Fig 2. Typical Output Characteristics

VDS

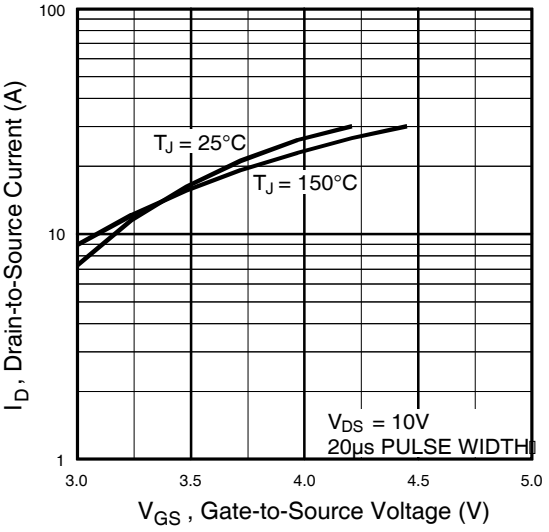


Fig 3. Typical Transfer Characteristics

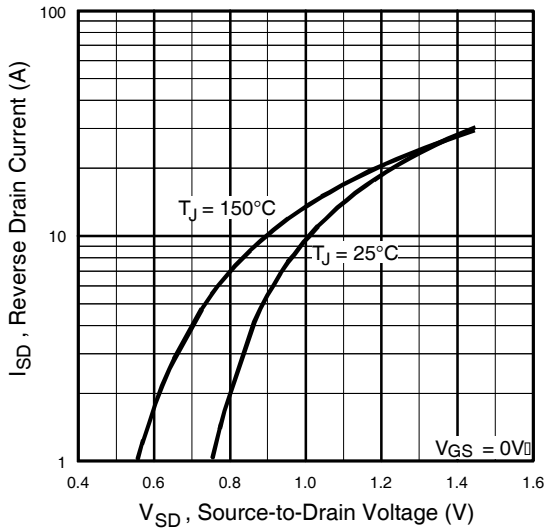


Fig 4. Typical Source-Drain Diode Forward Voltage

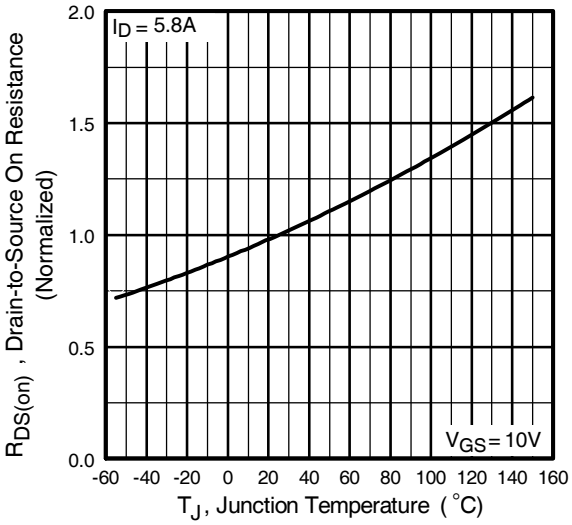


Fig 5. Normalized On-Resistance Vs. Temperature

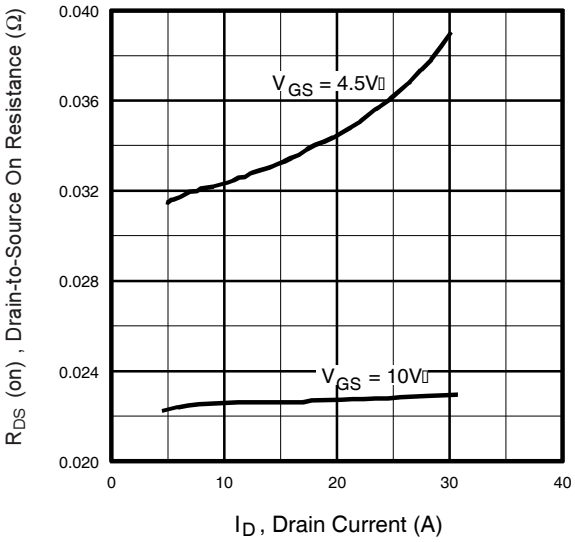


Fig 6. Typical On-Resistance Vs. Drain Current

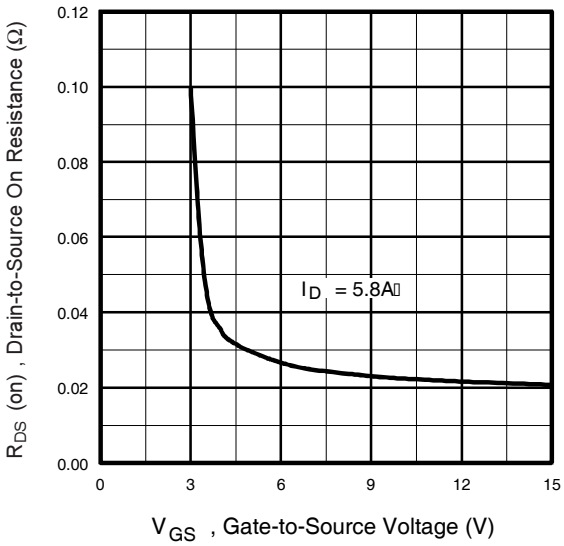


Fig 7. Typical On-Resistance Vs. Gate Voltage

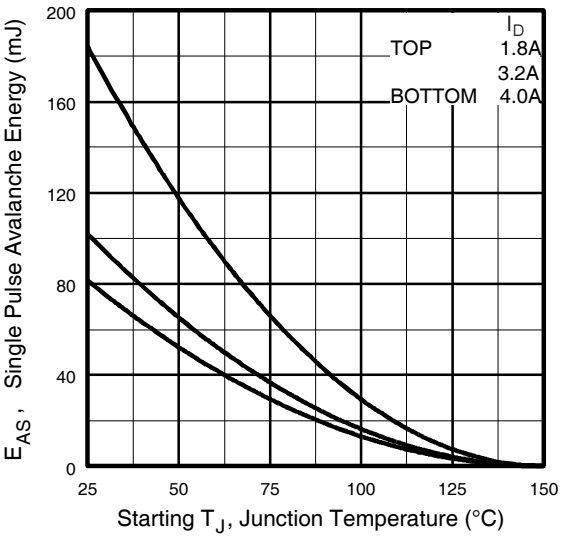


Fig 8. Maximum Avalanche Energy Vs. Drain Current

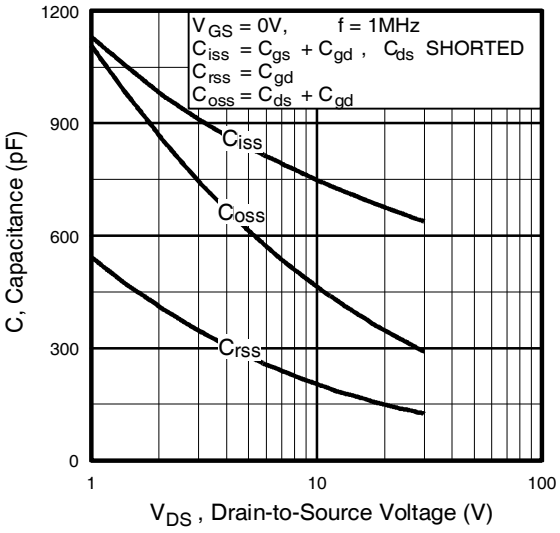


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

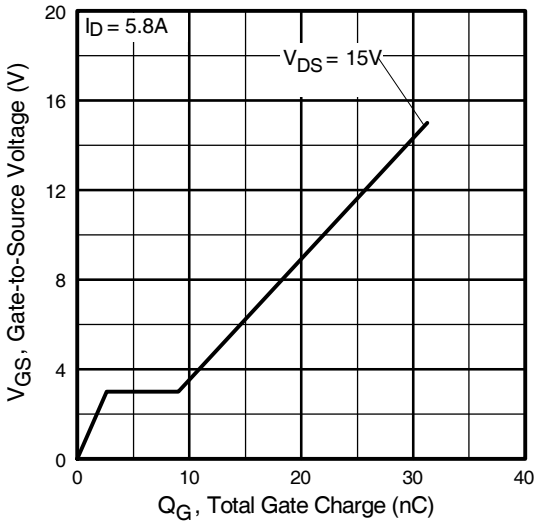


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

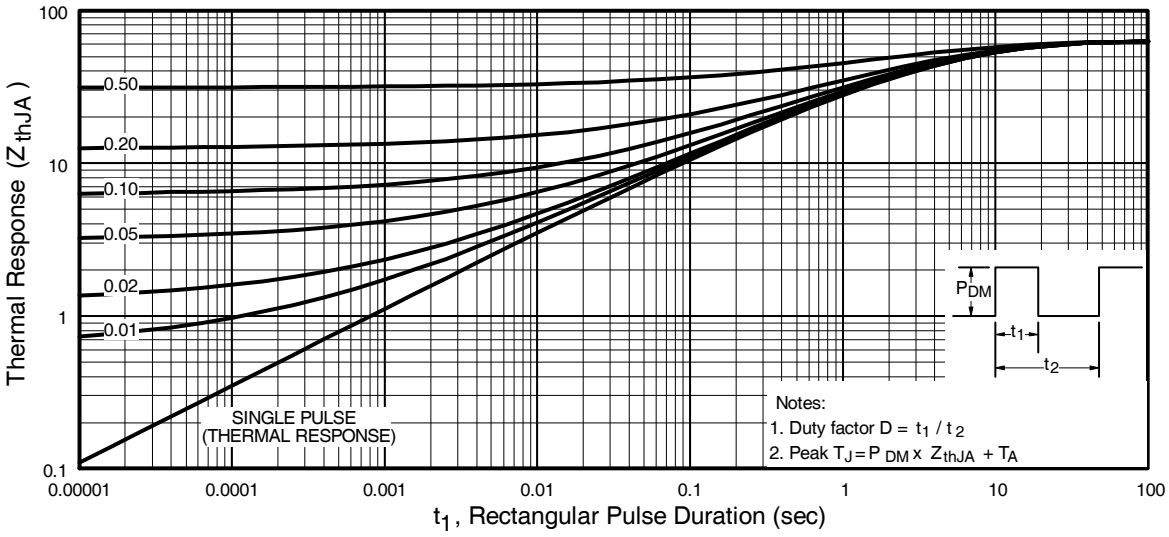
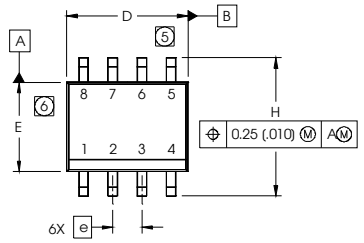
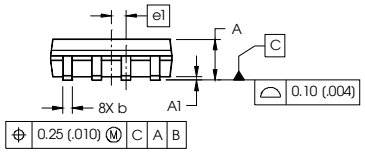


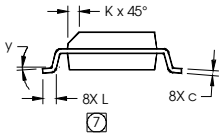
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SO-8 Package Outline

Dimensions are shown in milimeters (inches)







DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

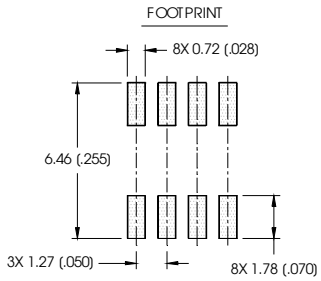
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).

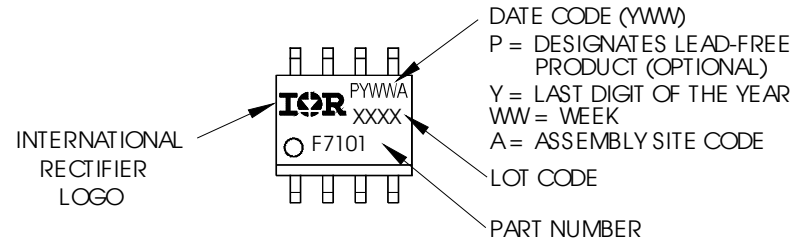
6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).

7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



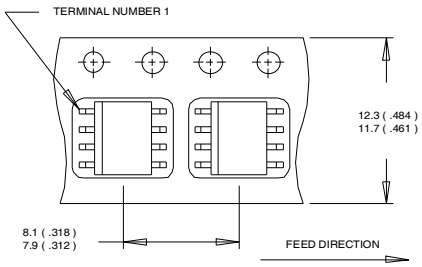
SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

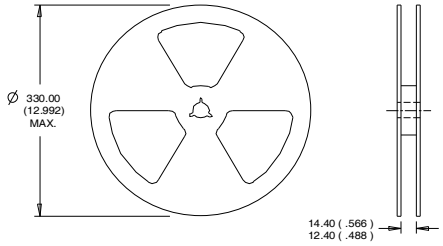


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel (Dimensions are shown in milimeters (inches))



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification information†

Qualification level	Industrial (per JEDEC JESD47F†† guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D††)
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability
†† Applicable version of JEDEC standard at the time of product release

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